

Silicon Schottky diode

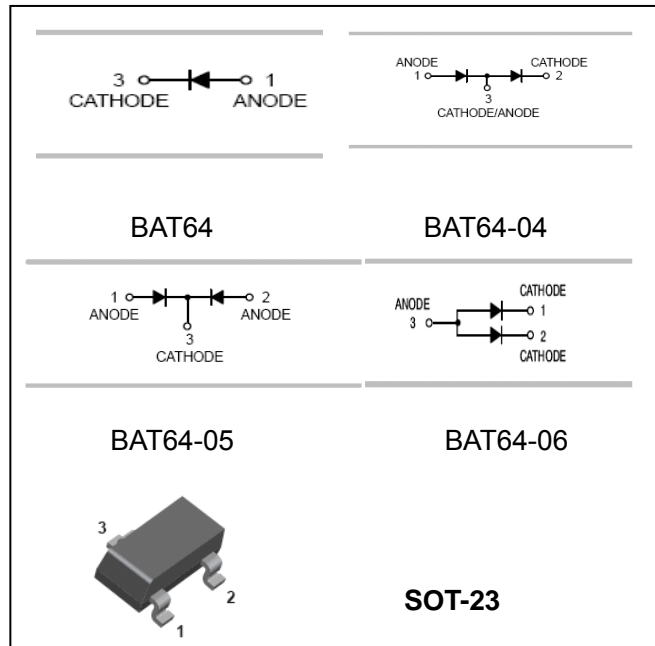
BAT64/-04/-05/-06

FEATURES

- For Low-loss,fast-recovery, Meter protection,bias isolation And clamping application.
- Low forward voltage.



Lead-free



ORDERING INFORMATION

Type No.	Marking	Package Code
BAT64	63	SOT-23
BAT64-04	64	SOT-23
BAT64-05	65	SOT-23
BAT64-06	66	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
Diode Reverse Voltage	V_R	40	V
Forward Current	I_F	250	mA
Non-Repetitive Peak Surge Forward Current	I_{FRM}	800	mA
Average Rectified Forward Current(50/60Hz,sinus)	I_{FAV}	120	mA
Power Dissipation	P_d	250	mW
Operating and Storage temperature	T_j, T_{STG}	-55 to +150	°C



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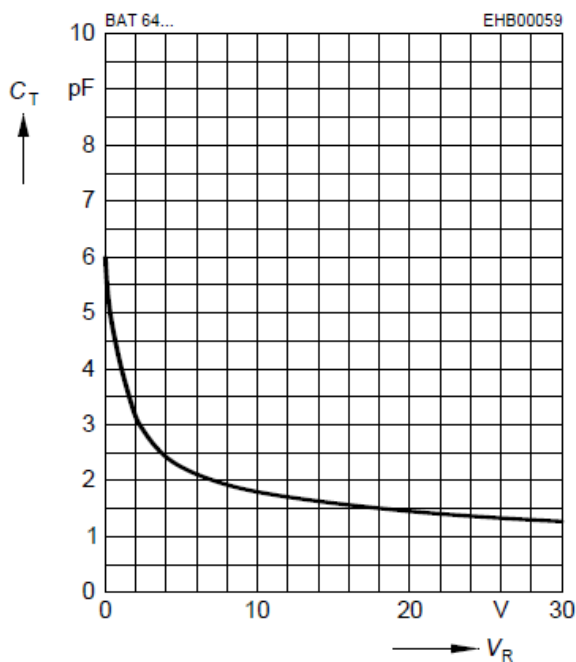
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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

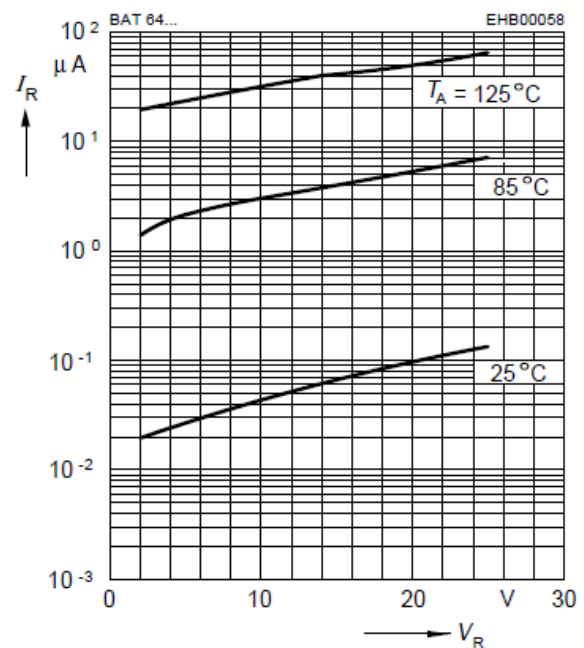
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)}$	40			V	$I_R=10\mu A$
Forward voltage	V_{F1}	0.27 0.30 0.37 0.5	0.32 0.385 0.44 0.57	0.35 0.43 0.52 0.75	V	$I_F=1mA$ $I_F=10mA$ $I_F=30mA$ $I_F=100mA$
Reverse current	I_R			2 200	μA	$V_R=30V$ $V_R=30V, T_A=85^\circ C$
Diode Capacitanc	C_T		4	6	pF	$V_R=1V, f=1MHz$
Reverse Recovery Time	t_{rr}			5	ns	$I_F=I_R=10mA$ $t_{rr}=0.1I_R, R_L=100\Omega$

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Diode capacitance $C_T = f(V_R)$
 $f = 1MHz$



Reverse current $I_R = f(V_R)$
 $T_A = \text{Parameter}$

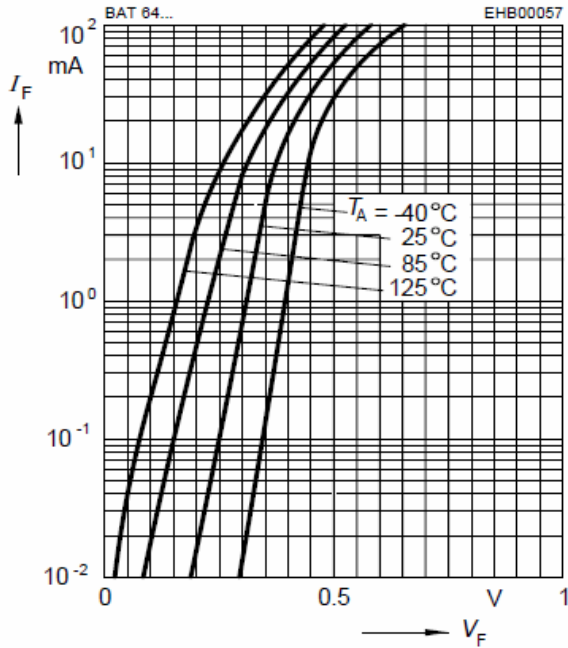


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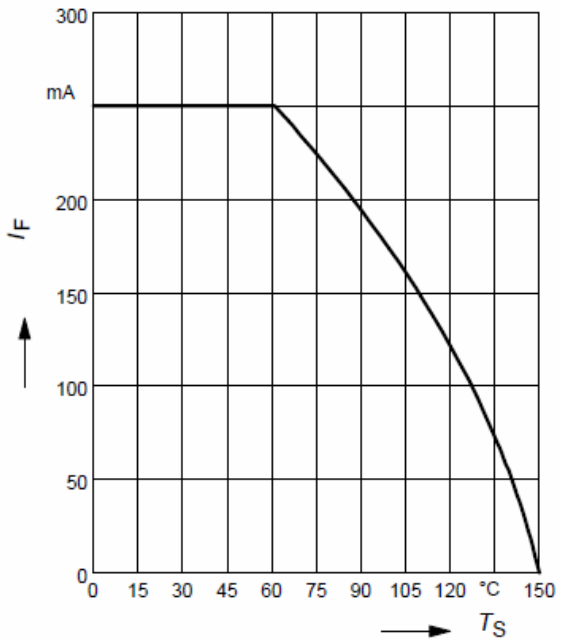
Forward current $I_F = f(V_F)$

$T_A =$ Parameter



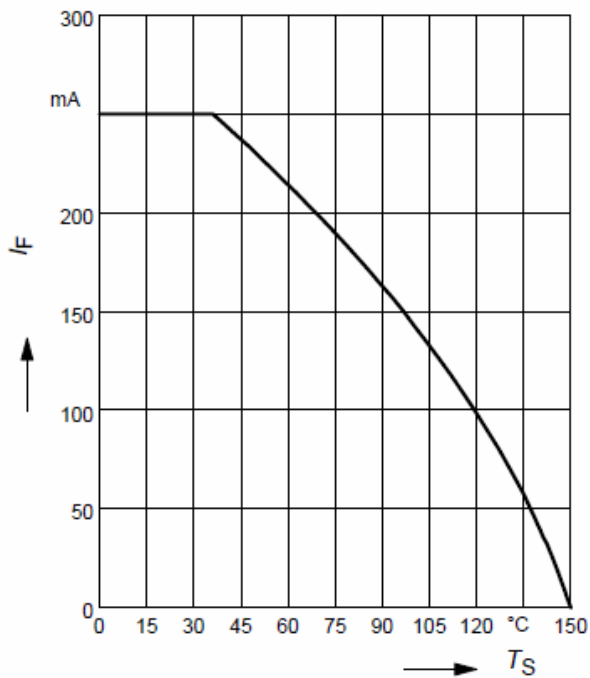
Forward current $I_F = f(T_S)$

BAT64-04, BAT64-06



Forward current $I_F = f(T_S)$

BAT64-05



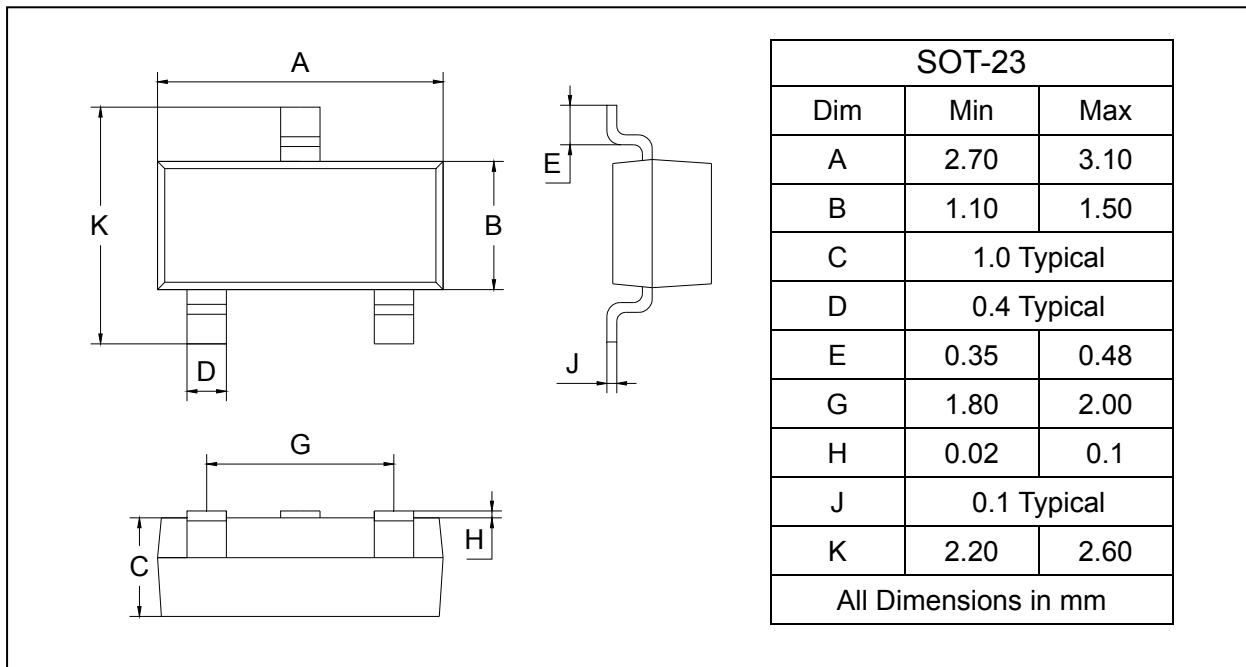
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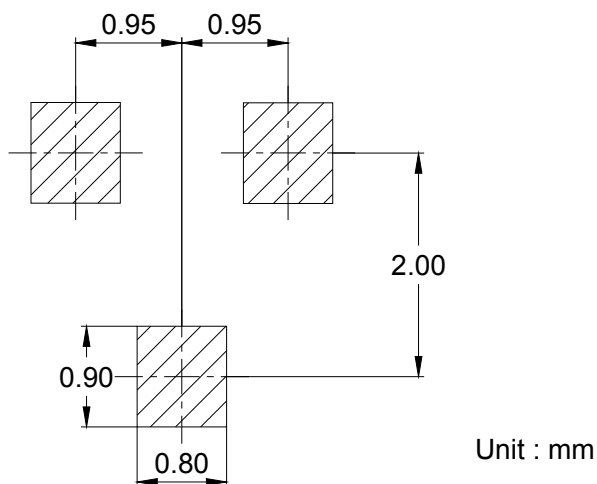
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BAT64/-04/-05/-06	SOT-23	3000/Tape&Reel